











SN74LVC2G66 SCES325N - JULY 2001 - REVISED AUGUST 2018

# SN74LVC2G66 Dual Bilateral Analog Switch

#### **Features**

- Available in the Texas Instruments NanoFree™ Package
- 1.65-V to 5.5-V V<sub>CC</sub> Operation
- Inputs Accept Voltages to 5.5 V
- Max  $t_{pd}$  of 0.8 ns at 3.3 V
- High On-Off Output Voltage Ratio
- High Degree of Linearity
- High Speed, Typically 0.5 ns  $(V_{CC} = 3 \text{ V}, C_{L} = 50 \text{ pF})$
- Rail-to-Rail Input/Output
- Low ON-State Resistance, Typically ≉6 Ω  $(V_{CC} = 4.5 \text{ V})$
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

### Applications

- Wireless Devices
- Audio and Video Signal Routing
- Portable Computing
- Wearable Devices
- Signal Gating, Chopping, Modulation or Demodulation (Modem)
- Signal Multiplexing for Analog-to-Digital and Digital-to-Analog Conversion Systems

# 3 Description

This dual bilateral analog switch is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

The SN74LVC2G66 device can handle both analog and digital signals. The SN74LVC2G66 device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction.

NanoFree package technology is breakthrough in IC packaging concepts, using the die as the package.

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section.

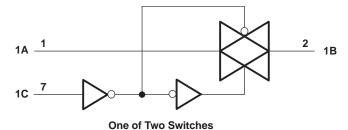
Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74LVC2G66DCT	SSOP (8)	2.95 mm × 2.80 mm		
SN74LVC2G66DCU	VSSOP (8)	2.30 mm × 2.00 mm		
SN74LVC2G66YZP	DSBGA (8)	1.91 mm × 0.91 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

## Logic Diagram, Each Switch (Positive Logic)







T:	aŀ	٦la	9 (	٦ſ	F (	$\Box$	n	n	t	ar	١ts
	αк	,,,		_		_	_		Ľ	_	

2				
_	Applications 1		8.2 Functional Block Diagram	13
3	Description 1		8.3 Feature Description	13
4	Revision History2		8.4 Device Functional Modes	13
5	Pin Configuration and Functions	9	Application and Implementation	14
6	Specifications		9.1 Application Information	14
U	6.1 Absolute Maximum Ratings		9.2 Typical Application	14
	6.2 ESD Ratings	10	Power Supply Recommendations	15
	6.3 Recommended Operating Conditions	11	Layout	16
	6.4 Thermal Information		11.1 Layout Guidelines	16
	6.5 Electrical Characteristics 5		11.2 Layout Example	
	6.6 Switching Characteristics 6	12	Device and Documentation Support	
	6.7 Analog Switch Characteristics		12.1 Community Resources	
	6.8 Operating Characteristics		12.2 Trademarks	
	6.9 Typical Characteristics		12.3 Electrostatic Discharge Caution	
7	• •		12.4 Glossary	
7 8	Parameter Measurement Information 8  Detailed Description	13	Mechanical, Packaging, and Orderable	
R	evision History			
OTE				
_	: Page numbers for previous revisions may differ from	page numb	ers in the current version.	
	•	page numb	pers in the current version.	Page
hanç	: Page numbers for previous revisions may differ from			
hanç	: Page numbers for previous revisions may differ from ges from Revision M (May 2018) to Revision N			
<b>hanç</b> Ch	: Page numbers for previous revisions may differ from ges from Revision M (May 2018) to Revision N			
Ch Ch	: Page numbers for previous revisions may differ from ges from Revision M (May 2018) to Revision N  nanged the YZP pin configuration	M		Page
Ch Ch Chang Up	Page numbers for previous revisions may differ from the sees from Revision M (May 2018) to Revision N ranged the YZP pin configuration	M		Page
Ch Ch Chang Ch	: Page numbers for previous revisions may differ from  ges from Revision M (May 2018) to Revision N  hanged the YZP pin configuration	M		Page 3
Ch Ch Chang Ch	Page numbers for previous revisions may differ from the sees from Revision M (May 2018) to Revision N ranged the YZP pin configuration	M		Page 3
Chang Chang Ch Ch	: Page numbers for previous revisions may differ from  ges from Revision M (May 2018) to Revision N  hanged the YZP pin configuration	M		Page 3

Typical Characteristics section, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation 

Changes from Revision J (December 2011) to Revision K

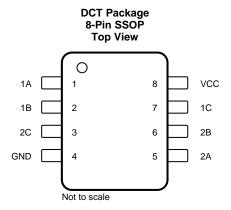
**Page** 

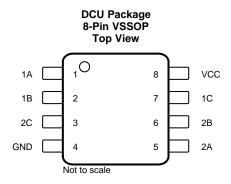
Submit Documentation Feedback

Copyright © 2001-2018, Texas Instruments Incorporated

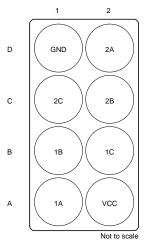


# 5 Pin Configuration and Functions





#### YZP Package 8-Pin DSBGA Bottom View



See mecahnical drawings for dimensions.

## **Pin Functions**

	PIN			
NAME	DCT DCU	YZP	I/O	DESCRIPTION
1A	1	A1	I/O	Bidirectional signal to be switched
1B	2	B1	I/O	Bidirectional signal to be switched
2C	3	C1	I	Controls the switch (L = OFF, H = ON)
2A	5	D2	I/O	Bidirectional signal to be switched
2B	6	C2	I/O	Bidirectional signal to be switched
1C	7	B2	I	Controls the switch (L = OFF, H = ON)
GND	4	D1	_	Ground pin
V <sub>CC</sub>	8	A2	_	Power pin



# 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage <sup>(2)</sup>		-0.5	6.5	V
$V_{I}$	Input voltage (2)(3)			6.5	V
Vo	Switch I/O voltage (2)(3)(4)		-0.5	$V_{CC} + 0.5$	V
I <sub>IK</sub>	Control input clamp current	V <sub>1</sub> < 0		-50	mA
I <sub>I/OK</sub>	I/O port diode current	$V_{I/O} < 0$ or $V_{I/O} > V_{CC}$		-50	mA
I <sub>T</sub>	On-state switch current	$V_{I/O} = 0$ to $V_{CC}$		±50	mA
	Continuous current through V <sub>CC</sub> or GND			±100	mA
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground, unless otherwise specified.

## 6.2 ESD Ratings

			VALUE	UNIT
	Floatroatatio	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	±2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

See (1).

			MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage		1.65	5.5	V	
V <sub>I/O</sub>	I/O port voltage		0	V <sub>CC</sub>	V	
		V <sub>CC</sub> = 1.65 V to 1.95 V	V <sub>CC</sub> × 0.65			
.,	High level in a trade or control in a t	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	$V_{CC} \times 0.7$		\ /	
$V_{IH}$	High-level input voltage, control input	V <sub>CC</sub> = 3 V to 3.6 V	$V_{CC} \times 0.7$		V	
		V <sub>CC</sub> = 4.5 V to 5.5 V	$V_{CC} \times 0.7$			
		V <sub>CC</sub> = 1.65 V to 1.95 V		V <sub>CC</sub> × 0.35		
	Low-level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		$V_{CC} \times 0.3$	V	
$V_{IL}$		V <sub>CC</sub> = 3 V to 3.6 V		$V_{CC} \times 0.3$	V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$V_{CC} \times 0.3$		
VI	Control input voltage		0	5.5	V	
		V <sub>CC</sub> = 1.65 V to 1.95 V		20		
A + / A > .	Input transition rise or fall time	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		20	ns/V	
Δt/Δv	Input transition rise or fall time	V <sub>CC</sub> = 3 V to 3.6 V		10		
		V <sub>CC</sub> = 4.5 V to 5.5 V		10		
T <sub>A</sub>	Operating free-air temperature		-40	85	°C	

All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

<sup>(3)</sup> The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

<sup>(4)</sup> This value is limited to 5.5 V maximum.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.4 Thermal Information

			SN74LVC2G66				
	THERMAL METRIC <sup>(1)</sup>	DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	UNIT		
		8 PINS	8 PINS	8 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	186.1	204.4	102	°C/W		
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	116.5	77	_	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	98.6	83.2	_	°C/W		
ΨЈТ	Junction-to-top characterization parameter	42.2	7.1	_	°C/W		
ΨЈВ	Junction-to-board characterization parameter	97.6	82.7	_	°C/W		
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance	n/a	n/a	_	°C/W		

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

# 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITION	V <sub>CC</sub>	MIN TYP(1)	MAX	UNIT	
			$I_S = 4 \text{ mA}$	1.65 V	12.5	30	
_	ON state quitab registance	$V_I = V_{CC}$ or GND,	$I_S = 8 \text{ mA}$	2.3 V	9	20	Ω
r <sub>on</sub>	ON-state switch resistance	V <sub>C</sub> = V <sub>IH</sub> (see Figure 3 and Figure 1)	I <sub>S</sub> = 24 mA	3 V	7.5	15	12
		,	I <sub>S</sub> = 32 mA	4.5 V	6	10	
			$I_S = 4 \text{ mA}$	1.65 V	85	120 <sup>(1)</sup>	
-	Peak ON-state resistance	$V_I = V_{CC}$ to GND,	$I_S = 8 \text{ mA}$	2.3 V	22	30 <sup>(1)</sup>	Ω
r <sub>on(p)</sub>	reak ON-state resistance	V <sub>C</sub> = V <sub>IH</sub> (see Figure 3 and Figure 1)	$I_S = 24 \text{ mA}$	3 V	12	20	12
			$I_S = 32 \text{ mA}$	4.5 V	7.5	15	
			$I_S = 4 \text{ mA}$	1.65 V		7	
۸۰	Difference of ON-state resistance	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$	$I_S = 8 \text{ mA}$	2.3 V		5	Ω
$\Delta r_{on}$	between switches	(see Figure 3 and Figure 1)	$I_S = 24 \text{ mA}$	3 V		3	
			$I_S = 32 \text{ mA}$	4.5 V		2	
		$V_I = V_{CC}$ and $V_O = GND$ or			±		
I <sub>S(off)</sub>	OFF-state switch leakage current	$V_I = GND$ and $V_O = V_{CC}$ , $V_C = V_{IL}$ (see Figure 4)		5.5 V		±0.1 <sup>(1)</sup>	μА
I <sub>S(on)</sub>	ON-state switch leakage current	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$ , $V_C$	= Open	5.5 V		±1	μА
'S(on)	Or state switch leakage current	(see Figure 5)		0.0 V		±0.1 <sup>(1)</sup>	μπ
I <sub>I</sub>	Control input current	$V_C = V_{CC}$ or GND		5.5 V		±1	μА
'	Control input current	AC = ACC OL QIAD		3.5 V		±0.1 <sup>(1)</sup>	μΛ
I <sub>CC</sub>	Supply current	$V_C = V_{CC}$ or GND		5.5 V		10	μА
icc	Зарру сапен	AC = ACC OL QIAD		3.5 V		1 <sup>(1)</sup>	μΛ
$\Delta I_{CC}$	Supply-current change	$V_C = V_{CC} - 0.6 \text{ V}$		5.5 V		500	μΑ
C <sub>ic</sub>	Control input capacitance			5 V	3.5		pF
C <sub>io(off)</sub>	Switch input / output capacitance			5 V	6		pF
C <sub>io(on)</sub>	Switch input / output capacitance			5 V	14		pF

(1)  $T_A = 25^{\circ}C$ 



# 6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM	FROM TO (OUTPUT)		V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V	
	(INFOI)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$t_{pd}^{(1)}$	A or B	B or A		2		1.2		8.0		0.6	ns
t <sub>en</sub> <sup>(2)</sup>	С	A or B	2.3	10	1.6	5.6	1.5	4.4	1.3	3.9	ns
t <sub>dis</sub> (3)	С	A or B	2.5	10.5	1.2	6.9	2	7.2	1.1	6.3	ns

<sup>(1)</sup> t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>pd</sub>. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

# 6.7 Analog Switch Characteristics

 $T_A = 25^{\circ}C$ 

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V <sub>CC</sub>	ТҮР	UNIT
				1.65 V	35	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	120	
			f <sub>in</sub> = sine wave (see Figure 6)	3 V	175	
Frequency response	A or B	D or A		4.5 V	195	MHz
(switch on)	AOIB	B or A		1.65 V	>300	IVITZ
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	>300	
			f <sub>in</sub> = sine wave (see Figure 6)	3 V	>300	
				4.5 V	>300	
				1.65 V	-58	
		$f_{in} = 1 \text{ MHz (sine v (see Figure 7)}$ $B \text{ or A}$ $C_{L} = 5 \text{ pF, } R_{L} = 50$	$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-58	
			(see Figure 7)	3 V	-58	dB
Crosstalk <sup>(1)</sup> (between switches)	A or B			4.5 V	-58	
	AUB		$C_L$ = 5 pF, $R_L$ = 50 $\Omega$ , $f_{in}$ = 1 MHz (sine wave) (see Figure 7)	1.65 V	-42	
				2.3 V	-42	
				3 V	-42	
				4.5 V	-42	
				1.65 V	35	
Crosstalk	С	A or D	$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	50	m\/
(control input to signal output)	C	A or B	f <sub>in</sub> = 1 MHz (square wave) (see Figure 8)	3 V	70	mV
				4.5 V	100	
				1.65 V	-58	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-58	
			f <sub>in</sub> = 1 MHz (sine wave) (see Figure 9)	3 V	-58	
Feedthrough attenuation	A or B	D or A	,	4.5 V	-58	dB
(switch off)	A OL R	B or A		1.65 V	-42	uв
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	
			f <sub>in</sub> = 1 MHz (sine wave) (see Figure 9)	3 V	-42	
			,	4.5 V	-42	

(1) Adjust fin voltage to obtain 0 dBm at input.

<sup>2)</sup> t<sub>PZL</sub> and t<sub>PZH</sub> are the same as t<sub>en</sub>.

<sup>(3)</sup> t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis</sub>.



# **Analog Switch Characteristics (continued)**

 $T_A = 25$ °C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V <sub>cc</sub>	ТҮР	UNIT
		B or A		1.65 V	0.1%	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$ $f_{in} = 1 \text{ kHz}$ (sine wave) (see Figure 10)	2.3 V	0.025%	
	A or B			3 V	0.015%	
Sine-wave distortion				4.5 V	0.01%	
Sille-wave distortion			$C_L$ = 50 pF, $R_L$ = 10 k $\Omega$ , $f_{in}$ = 10 kHz (sine wave) (see Figure 10)	1.65 V	0.15%	
				2.3 V	0.025%	
				3 V	0.015%	
				4.5 V	0.01%	

# 6.8 Operating Characteristics

 $T_A = 25$ °C

PARAMETER		TEST	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT
		CONDITIONS	TYP	TYP	TYP	TYP	UNII
$C_{pd}$	Power dissipation capacitance	f = 10 MHz	8	9	9.5	11	pF

# 6.9 Typical Characteristics

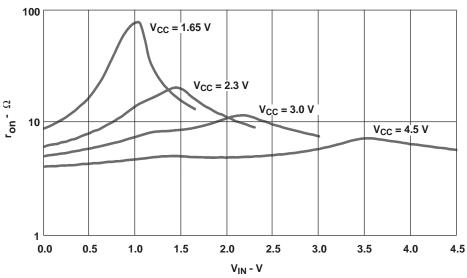
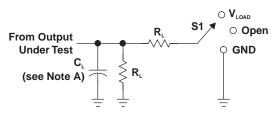


Figure 1. Typical  $r_{on}$  as a Function of Input Voltage (V<sub>I</sub>) for  $V_{I} = 0$  to  $V_{CC}$ 

Submit Documentation Feedback



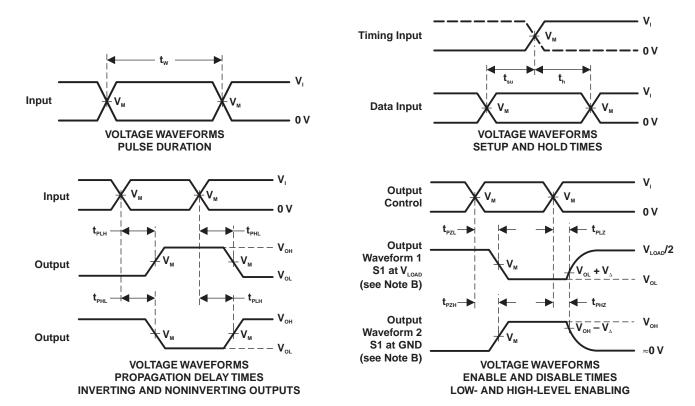
### 7 Parameter Measurement Information



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	V <sub>LOAD</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

п	0	Δ	ח	C	IR	CI	П	IT

V	INF	PUTS	V	V		В	\ \ \	
V <sub>cc</sub>	V,	t,/t,	V <sub>M</sub>	<b>V</b> <sub>LOAD</sub>	C <sub>L</sub>	R <sub>⊾</sub>	$V_{_{\Delta}}$	
$1.8~\textrm{V}\pm0.15~\textrm{V}$	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	<b>1 k</b> Ω	0.15 V	
2.5 V $\pm$ 0.2 V	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	500 Ω	0.15 V	
3.3 V $\pm$ 0.3 V	$V_{cc}$	≤2.5 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	50 pF	<b>500</b> Ω	0.3 V	
5 V $\pm$ 0.5 V	V <sub>cc</sub>	≤2.5 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	50 pF	500 Ω	0.3 V	



NOTES: A. C<sub>∟</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators have the following characteristics: PRR  $\leq$  10 MHz,  $Z_o = 50~\Omega$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{\mbox{\tiny PLH}}$  and  $t_{\mbox{\tiny PHL}}$  are the same as  $t_{\mbox{\tiny pd}}$
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

Submit Documentation Feedback

Copyright © 2001–2018, Texas Instruments Incorporated



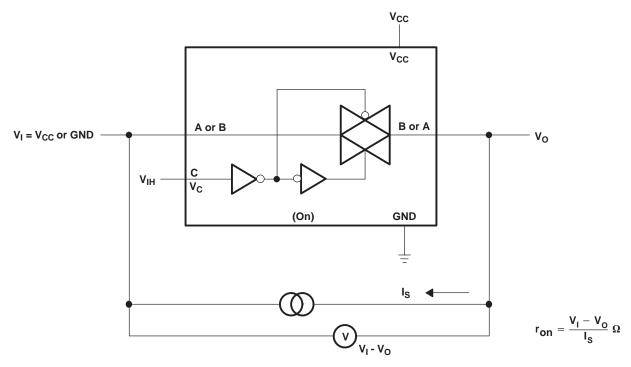


Figure 3. ON-State Resistance Test Circuit

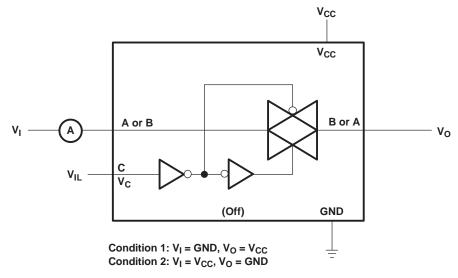


Figure 4. OFF-State Switch Leakage-Current Test Circuit



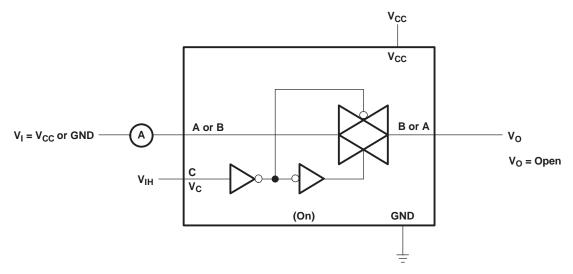


Figure 5. ON-State Leakage-Current Test Circuit

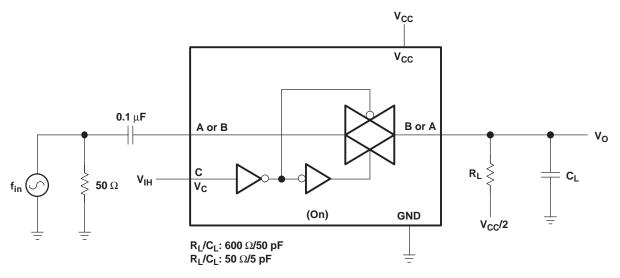


Figure 6. Frequency Response (Switch On)



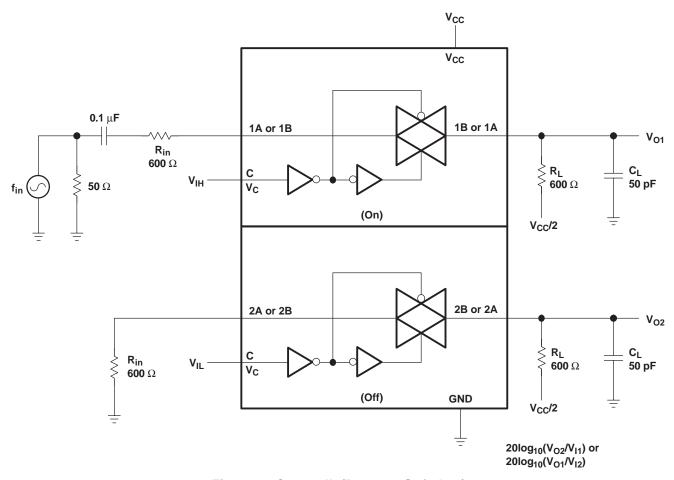


Figure 7. Crosstalk (Between Switches)

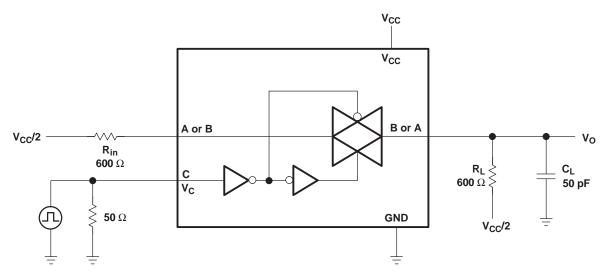


Figure 8. Crosstalk (Control Input, Switch Output)



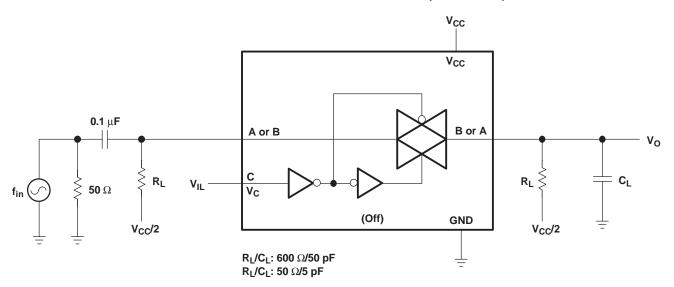


Figure 9. Feedthrough (Switch Off)

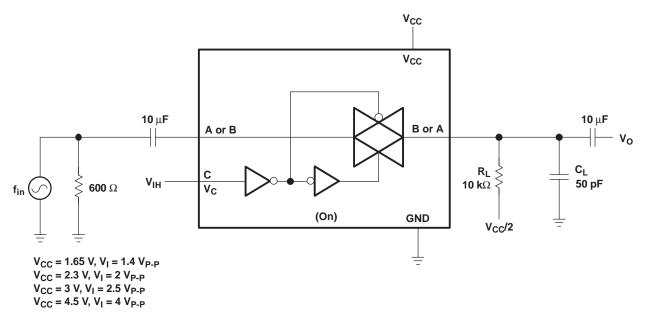


Figure 10. Sine-Wave Distortion

Submit Documentation Feedback



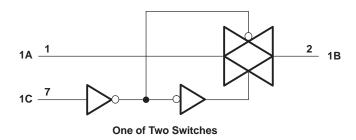
## 8 Detailed Description

#### 8.1 Overview

This dual bilateral analog switch is designed for 1.65-V to 5.5-V  $V_{CC}$  operation. Robust LVC family technology allows this device to accept input voltages without connecting power to  $V_{CC}$ .

The SN74LVC2G66 device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction. A high-level voltage applied to the control pin C enables the respective switch to begin propagating signals across the device. A low-level voltage disables this transmission. Each device incorporates two switches with independent control and operation.

# 8.2 Functional Block Diagram



### 8.3 Feature Description

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section. When C is this Signals can pass through A to B or B to A. Low ON-resistance of 6  $\Omega$  at 4.5-V V<sub>CC</sub> is ideal for analog signal conditioning systems. The control signals can accept voltages up to 5.5 V without V<sub>CC</sub> connected in the system. Combination of lower t<sub>pd</sub> of 0.8 ns at 3.3 V and low enable and disable time make this part suitable for high-speed signal switching applications.

#### 8.4 Device Functional Modes

Copyright © 2001-2018, Texas Instruments Incorporated

Table 1 lists the functional modes of the SN74LVC2G66.

**Table 1. Function Table** 

CONTROL INPUT (C)	SWITCH
L	Off
Н	On



# 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

# 9.1 Application Information

The SN74LVC2G66 can be used in any situation where an Dual SPST switch would be used and a solid-state, voltage controlled version is preferred.

## 9.2 Typical Application

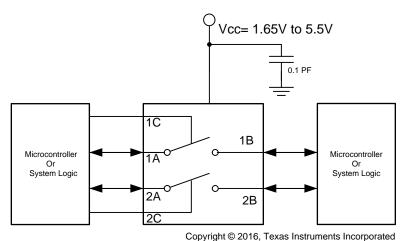


Figure 11. Typical Application Schematic

#### 9.2.1 Design Requirements

The SN74LVC2G66 allows on/off control of analog and digital signals with a digital control signal. All input signals should remain between 0 V and  $V_{CC}$  for optimal operation.

#### 9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
  - For rise time and fall time specifications, see  $\Delta t/\Delta v$  in the Recommended Operating Conditions table.
  - For specified high and low levels, see V<sub>IH</sub> and V<sub>IL</sub> in the Recommended Operating Conditions table.
  - Inputs and outputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V<sub>CC</sub>.
- 2. Recommended Output Conditions:
  - Load currents should not exceed ±50 mA.
- 3. Frequency Selection Criterion:
  - Maximum frequency tested is 150 MHz.
  - Added trace resistance or capacitance can reduce maximum frequency capability; use layout practices as directed in *Layout*.

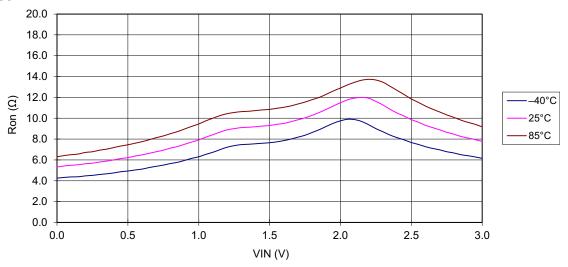
Submit Documentation Feedback

Copyright © 2001–2018, Texas Instruments Incorporated



# **Typical Application (continued)**

#### 9.2.3 Application Curve



Pin: A-B,  $V_{CC} = 3 \text{ V}$ ,  $I_S = 24 \text{ mA}$ 

Figure 12. ron vs VI

# 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu F$  bypass capacitor is recommended. If there are multiple pins labeled  $V_{CC}$ , then a 0.01- $\mu F$  or 0.022- $\mu F$  capacitor is recommended for each  $V_{CC}$  because the VCC pins will be tied together internally. For devices with dual-supply pins operating at different voltages, for example  $V_{CC}$  and  $V_{DD}$ , a 0.1- $\mu F$  bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- $\mu F$  and 1- $\mu F$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.



# 11 Layout

## 11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self–inductance of the trace — resulting in the reflection.

#### **NOTE**

Not all PCB traces can be straight, and so they will have to turn corners. Figure 13 shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

## 11.2 Layout Example

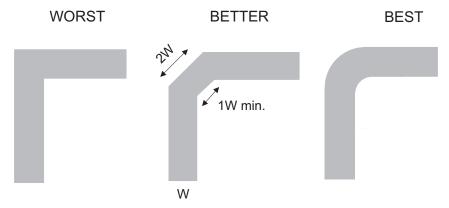


Figure 13. Trace Example

16

Submit Documentation Feedback



# 12 Device and Documentation Support

#### 12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.2 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

### 12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

# 12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

# 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 10-Nov-2025

#### PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC2G66DCTR	Active	Production	SSOP (DCT)   8	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)
SN74LVC2G66DCTR.A	Active	Production	SSOP (DCT)   8	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)
SN74LVC2G66DCTR.B	Active	Production	SSOP (DCT)   8	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)
SN74LVC2G66DCUR	Active	Production	VSSOP (DCU)   8	3000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ
SN74LVC2G66DCUR.A	Active	Production	VSSOP (DCU)   8	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ
SN74LVC2G66DCUR.B	Active	Production	VSSOP (DCU)   8	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ
SN74LVC2G66DCURG4	Active	Production	VSSOP (DCU)   8	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCURG4.B	Active	Production	VSSOP (DCU)   8	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCUT	Obsolete	Production	VSSOP (DCU)   8	-	-	Call TI	Call TI	-40 to 85	(C66Q, C66R)
SN74LVC2G66DCUTE4	Active	Production	VSSOP (DCU)   8	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCUTG4	Active	Production	VSSOP (DCU)   8	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66DCUTG4.B	Active	Production	VSSOP (DCU)   8	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R
SN74LVC2G66YZPR	Active	Production	DSBGA (YZP)   8	3000   LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C67, C6N)
SN74LVC2G66YZPR.B	Active	Production	DSBGA (YZP)   8	3000   LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C67, C6N)

<sup>(1)</sup> **Status:** For more details on status, see our product life cycle.

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

# **PACKAGE OPTION ADDENDUM**

www.ti.com 10-Nov-2025

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74LVC2G66:

Automotive: SN74LVC2G66-Q1

NOTE: Qualified Version Definitions:

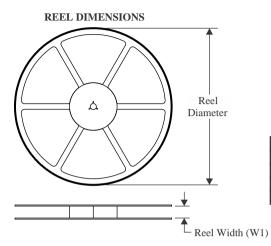
Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

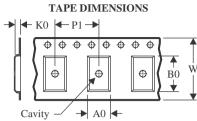
**PACKAGE MATERIALS INFORMATION** 

www.ti.com 14-May-2025

## TAPE AND REEL INFORMATION

NSTRUMENTS





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

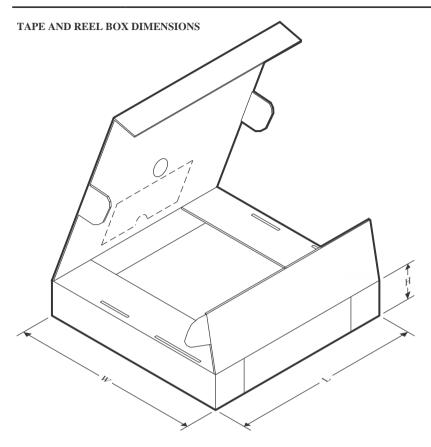


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G66DCTR	SSOP	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



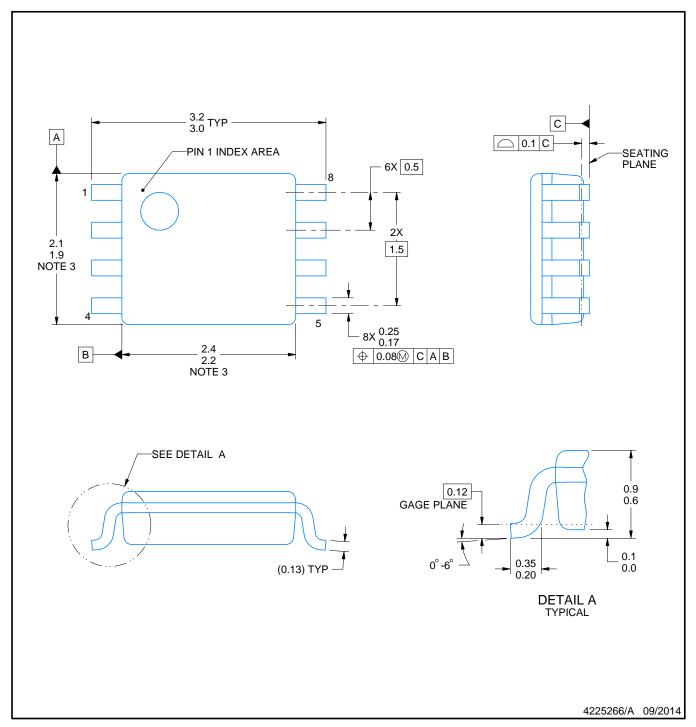
www.ti.com 14-May-2025



#### \*All dimensions are nominal

7 til dillionorono di o mominidi							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G66DCTR	SSOP	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0





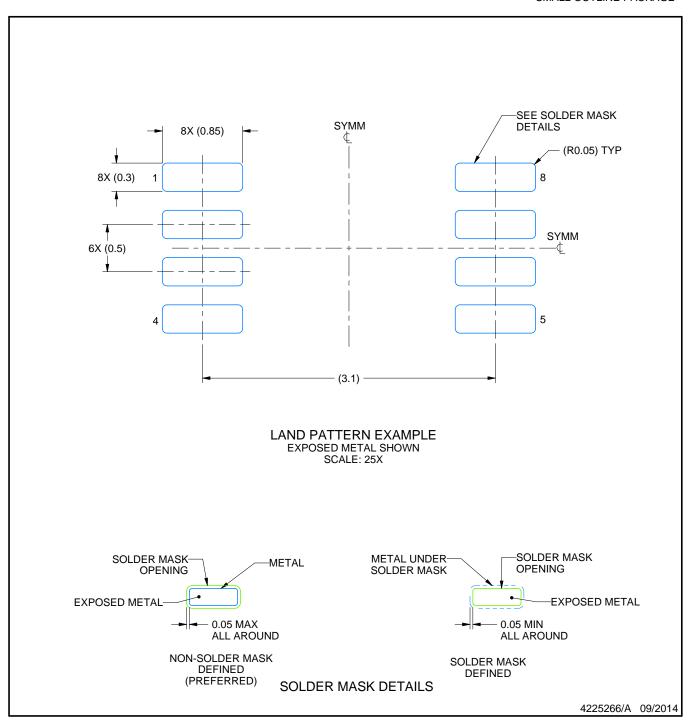
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
  4. Reference JEDEC registration MO-187 variation CA.

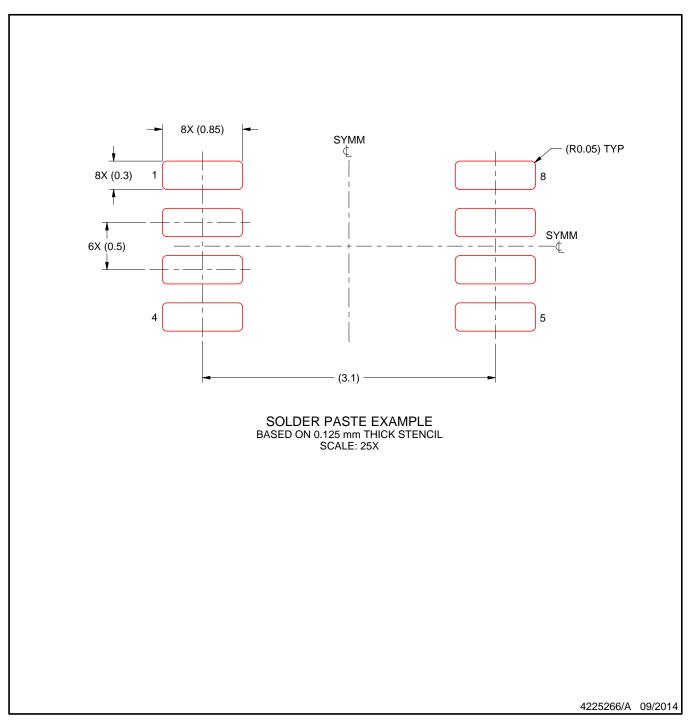




NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



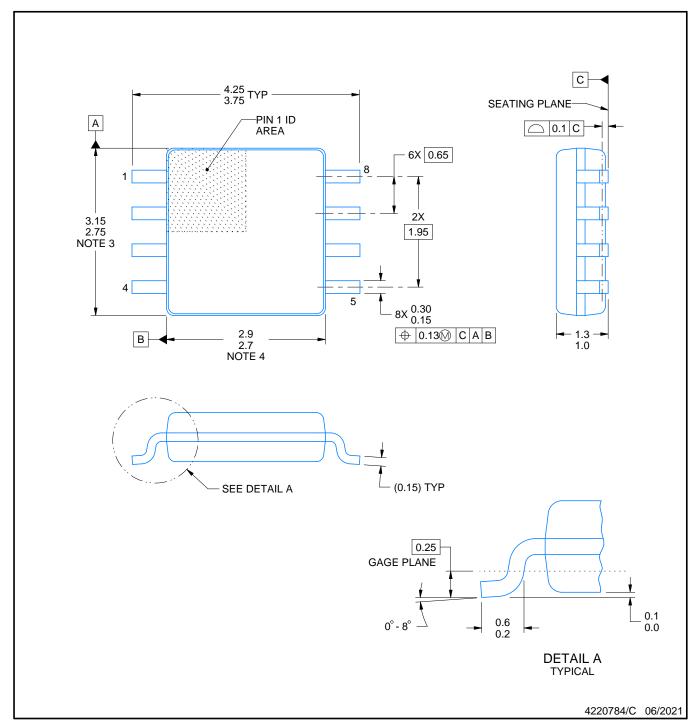


NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.







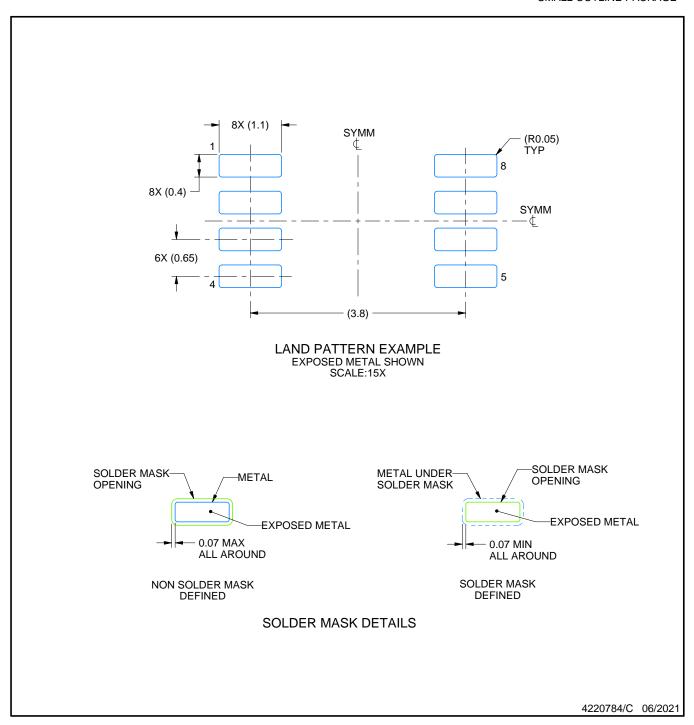
#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.

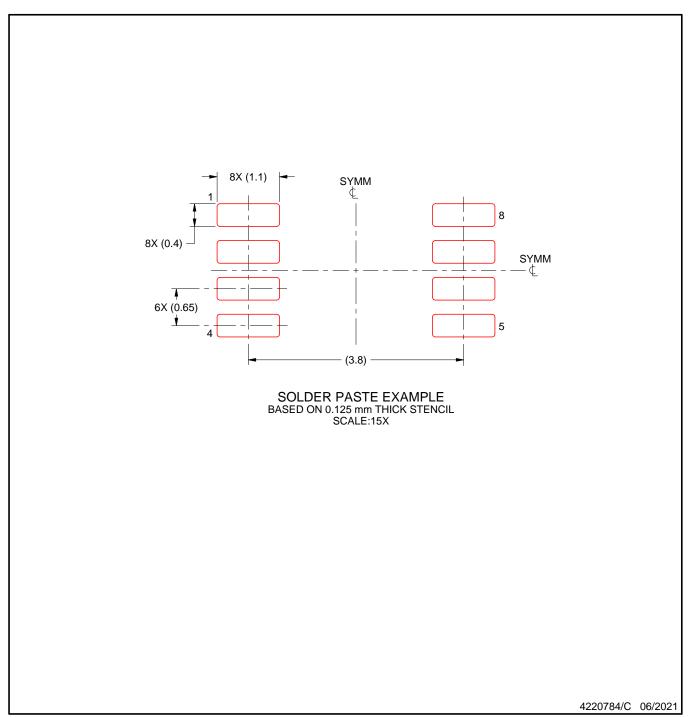




NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





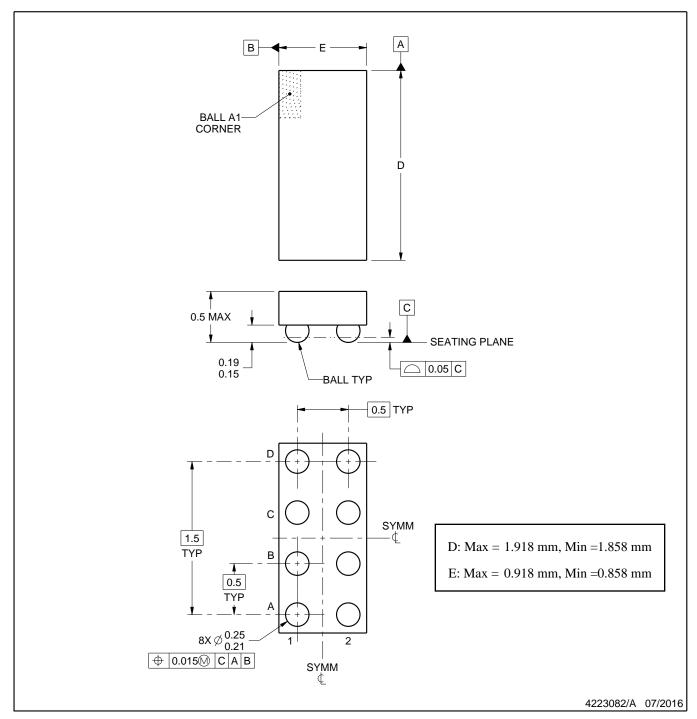
NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY

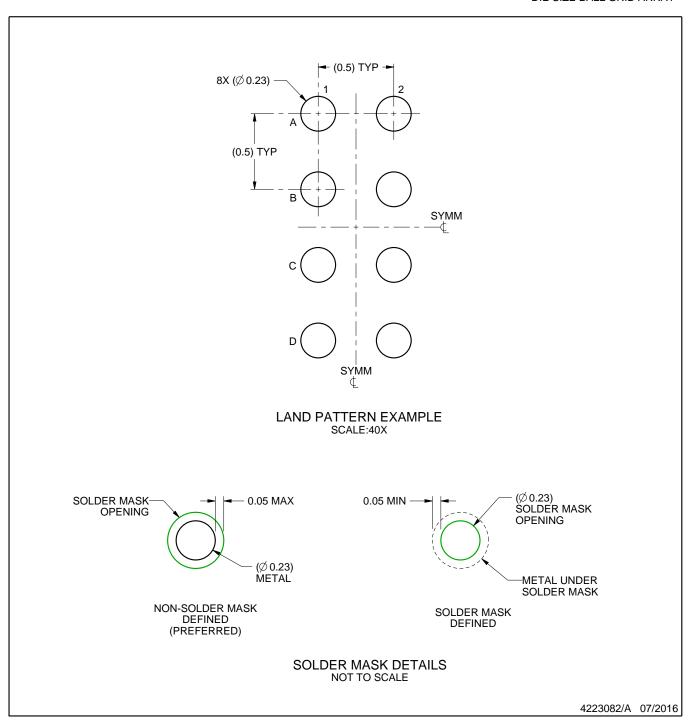


### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

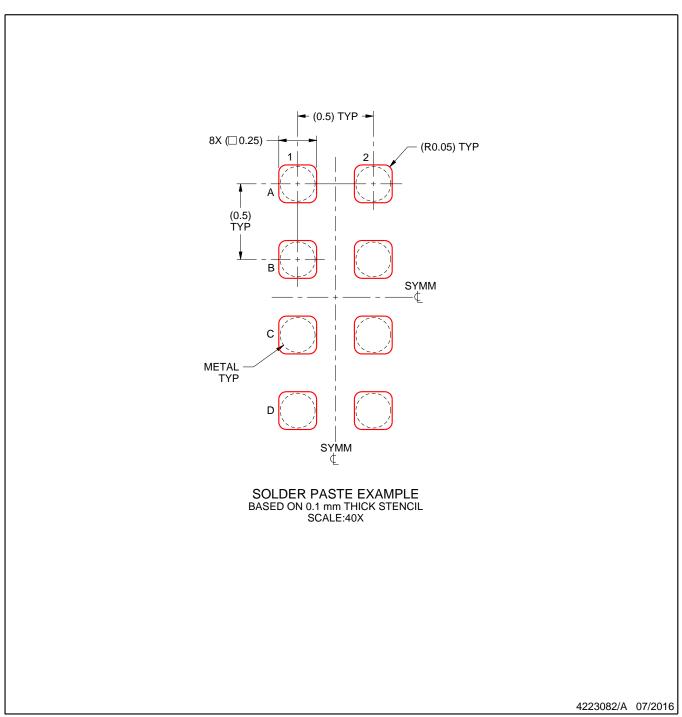


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



#### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025